

RGTV00TK65 650V 50A Field Stop Trench IGBT

V _{CES}	650V
Ι _{C (100°C)}	26A
V _{CE(sat) (Typ.)}	1.5V@I _c =50A
P _D	94W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching & Low Switching Loss
- 3) Short Circuit Withstand Time 2µs
- 4) Pb free Lead Plating ; RoHS Compliant

Applications

Solar Inverter

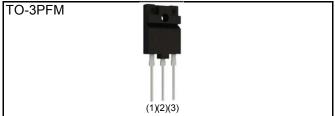
UPS

Welding

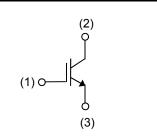
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PFC

Outline



Inner Circuit



(1) Gate (2) Collector (3) Emitter

Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Tuno	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGTV00TK65

•Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

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Paramete	Symbol	Value	Unit	
Collector - Emitter Voltage	V _{CES}	650	V	
Gate - Emitter Voltage	V _{GES}	±30	V	
Collector Current	$T_{\rm C}$ = 25°C	Ι _C	45	А
Collector Current	T _C = 100°C	۱ _C	26	А
Pulsed Collector Current	I _{CP} *1	200	А	
Dower Dissinction	T _C = 25°C	P _D	94	W
Power Dissipation	T _C = 100°C	P _D	47	W
Operating Junction Temperatu	Tj	-40 to +175	°C	
Storage Temperature	T _{stg}	–55 to +175	°C	

*1 Pulse width limited by T_{jmax}.

•Thermal Resistance

Parameter	Symbol	Values			Unit
	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance IGBT Junction - Case	R _{θ(j-c)}	-	-	1.59	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
Farameter	Symbol	Conditions	Min.	Тур.	Max.	Onit
Collector - Emitter Breakdown Voltage	BV _{CES}	I _C = 10μΑ, V _{GE} = 0V	650	-	-	V
Collector Cut - off Current	I _{CES}	V _{CE} = 650V, V _{GE} = 0V	-	-	10	μA
Gate - Emitter Leakage Current	I _{GES}	V _{GE} = ±30V, V _{CE} = 0V	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	V _{CE} = 5V, I _C = 34.3mA	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	I _C = 50A, V _{GE} = 15V T _j = 25°C T _j = 175°C	-	1.5 1.85	1.9 -	V

•IGBT Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Deremeter	Queebal	Symbol		Values			
Parameter	Symbol	Conditions	Min. Typ. Max.		Max.	– Unit	
Input Capacitance	C _{ies}	V _{CE} = 30V	-	2890	-		
Output Capacitance	C _{oes}	V _{GE} = 0V	-	116	-	pF	
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	48	-		
Total Gate Charge	Qg	V _{CE} = 400V	-	104	-		
Gate - Emitter Charge	Q _{ge}	I _C = 50A	-	21	-	nC	
Gate - Collector Charge	Q _{gc}	V _{GE} = 15V	-	37	-		
Turn - on Delay Time	t _{d(on)}	I _C = 50A, V _{CC} = 400V	-	41	-		
Rise Time	t _r	V _{GE} = 15V, R _G = 10Ω	-	20	-		
Turn - off Delay Time	t _{d(off)}	T _j = 25°C	-	142	-	ns	
Fall Time	t _f	Inductive Load	-	38	-		
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	1.17	-	ml	
Turn - off Switching Loss	E _{off}	reverse recovery	-	0.94	-	mJ	
Turn - on Delay Time	t _{d(on)}	I _C = 50A, V _{CC} = 400V	-	39	-		
Rise Time	t _r	V _{GE} = 15V, R _G = 10Ω	-	23	-		
Turn - off Delay Time	t _{d(off)}	T _j = 175°C	-	167	-	ns	
Fall Time	t _f	Inductive Load	-	80	-		
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	1.25	-	ml	
Turn - off Switching Loss	E _{off}	reverse recovery	-	1.28	-	mJ	
		I _C = 200A, V _{CC} = 520V					
Reverse Bias Safe Operating Area	RBSOA	V _P = 650V, V _{GE} = 15V	FU	LL SQUA	RE	-	
		R _G = 100Ω, T _j = 175°C					
		$V_{CC} \leq 360V$					
Short Circuit Withstand Time	t _{sc}	V _{GE} = 15V	2	-	-	μs	
		T _j = 25°C					

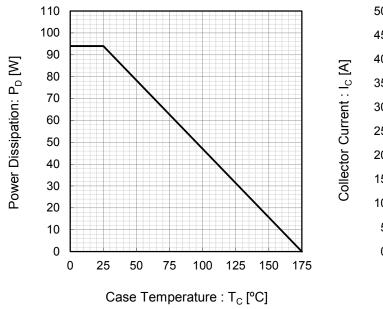


Fig.1 Power Dissipation vs. Case Temperature

Fig.2 Collector Current vs. Case Temperature

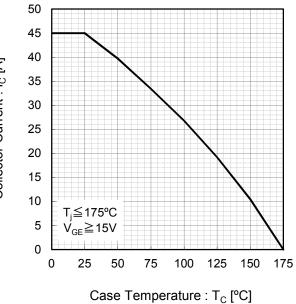
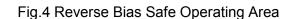
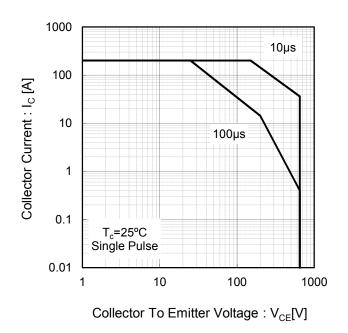
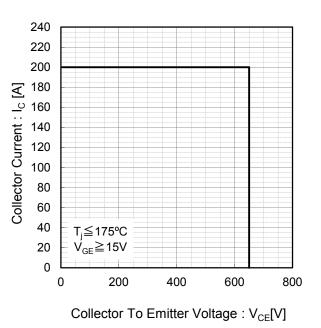


Fig.3 Forward Bias Safe Operating Area







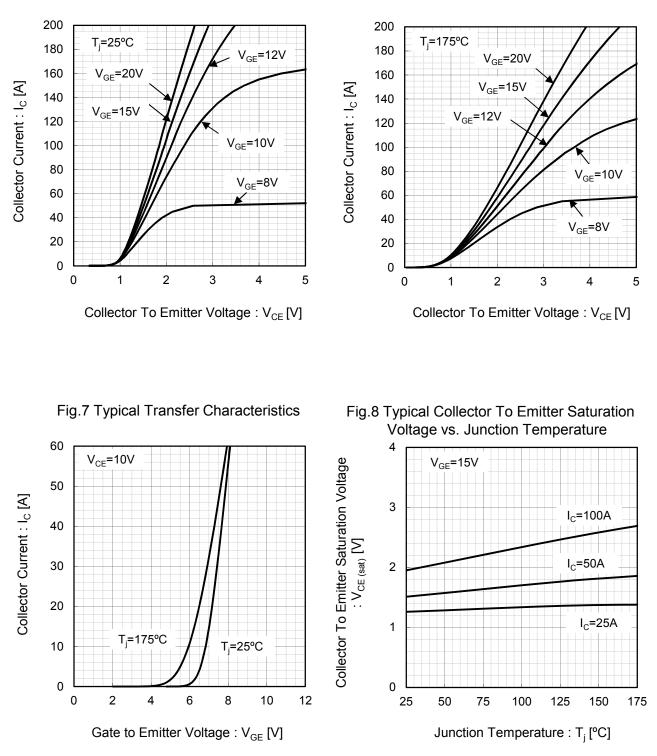
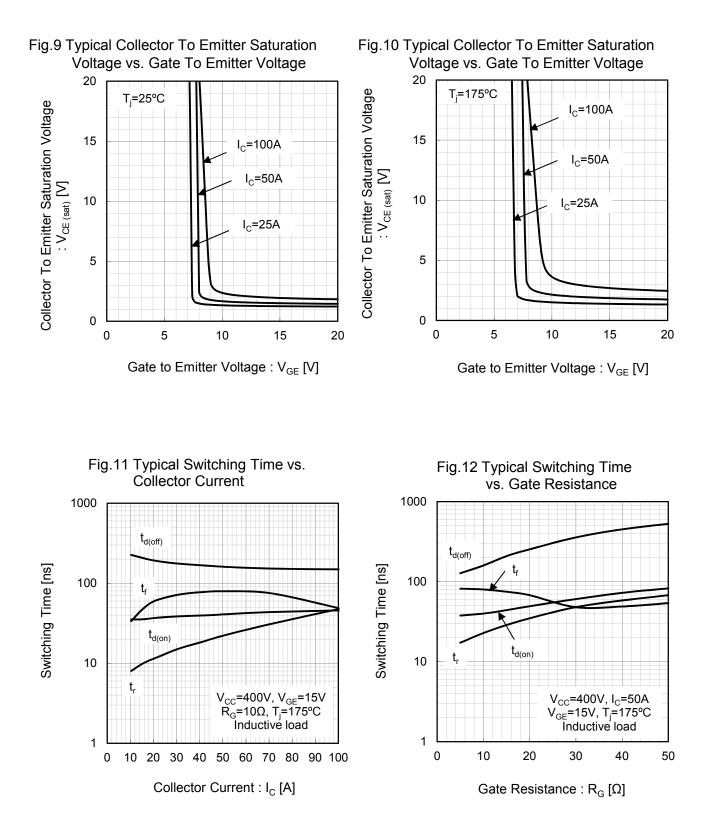
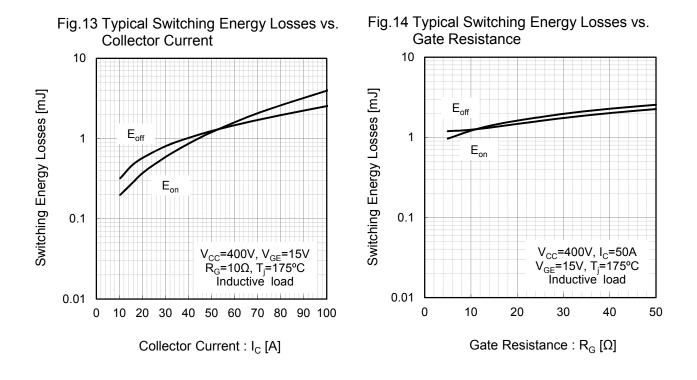


Fig.5 Typical Output Characteristics

Fig.6 Typical Output Characteristics





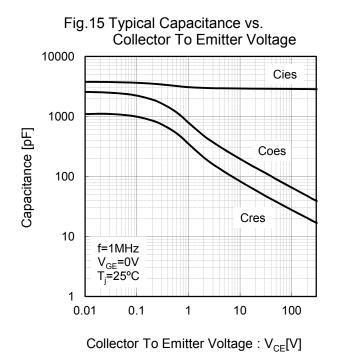
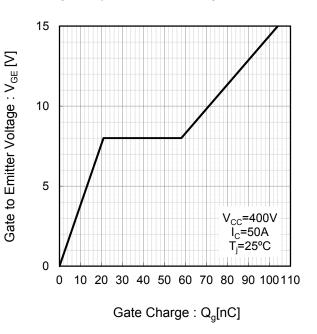


Fig.16 Typical Gate Charge



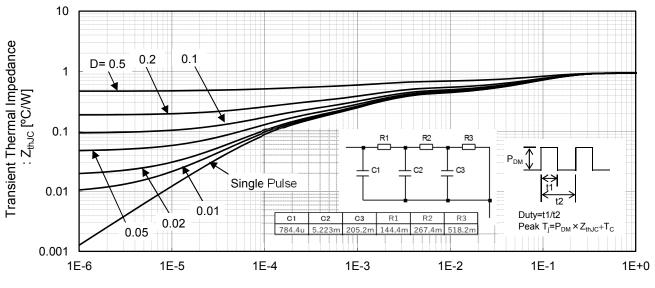
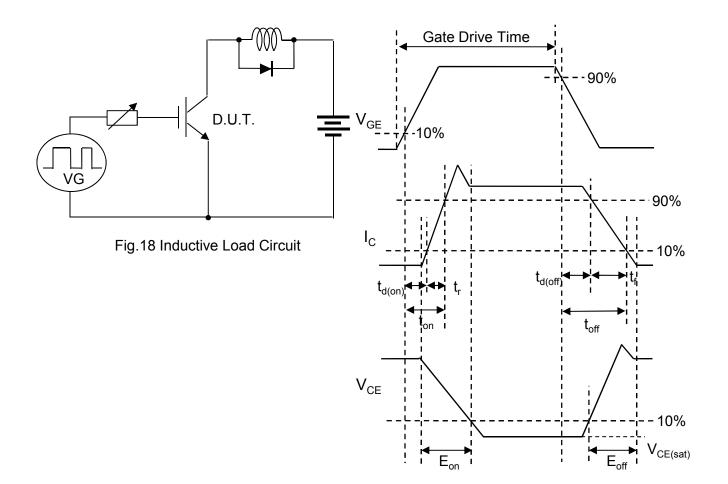
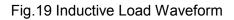


Fig.17 Typical IGBT Transient Thermal Impedance

Pulse Width : t1[s]

Inductive Load Switching Circuit and Waveform





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RGTV00TK65 - Web Page

Distribution Inventory

Part Number	RGTV00TK65
Package	TO-3PFM
Unit Quantity	450
Minimum Package Quantity	30
Packing Type	Tube
Constitution Materials List	inquiry
RoHS	Yes